H.T.No.

Code No: EC1527 GEC-R14

III B. Tech I Semester Supplementary Examinations, July 2017 LINEAR AND DIGITAL ICs

(Electronics and Communication Engineering)

Time: 3 Hours Max. Marks: 60

Note: All Questions from PART-A are to be answered at one place.

Answer any **FOUR** questions from **PART-B.** All Questions carry equal Marks.

PART-A

 $6 \times 2 = 12M$

- 1. Draw an equivalent circuit and list out various Ideal and Practical specifications of an op-amp.
- 2. Obtain open loop and closed loop gain expression for an inverting and non-inverting amplifier.
- 3. Write the difference between two types of ADCs.
- 4. Derive the voltage to frequency conversion factor for VCO.
- 5. Draw the logic symbol and truth table for IC 74×139.
- 6. Sketch 1-bit DRAM cell and explain its operation.

PART-B

 $4 \times 12 = 48M$

- 1. a) With neat diagram, explain the functionality of each basic building blocks of an op-amp. (6M)
 - b) Develop gain versus frequency response curves for external frequency compensation with different slope decades. (6M)
- 2. a) Derive the V₀ expression for ANTI LOG amplifier using IC741. (6M)
 - b) Explain how an op-amp can be used for converting V to I and I to V. (6M)
- 3. a) Design R-2R ladder DAC circuit using IC741 and explain its operation.

(6M)

- b) Explain the operation of SAR-ADC technique with suitable example. (6M)
- 4. a) Derive the Time period oscillations expression for monostable multi vibrator using IC555. (6M)
 - b) Explain about various blocks used in PLL and derive the equation for error voltage $V_{\rm e}$. (6M)

- 5. a) Draw the logic diagram of IC 74×283 and design a 24-bit ripple adder using the same IC. (6M)
 - b) Design a modulo 100 counter using two 74x163 binary counters. (6M)
- 6. a) Explain various timing parameters and applications of ROM. (6M)
 - b) Draw an internal structure of SRAM and explain its operation. (6M)
